2ST2121

Preliminary data

High power PNP epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = 250 V
- Complementary to 2ST5949 W.DZSC.COM
- Fast switching speed
- Typical f_t = 25 MHz
- Fully characterized at 125 °C

Applications

Audio power amplifier

Description

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

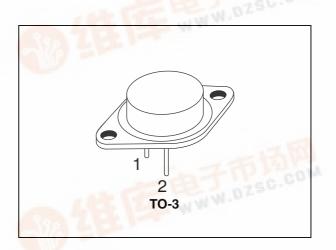


Figure 1. Internal schematic diagram

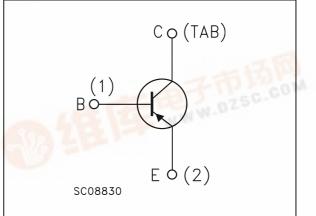


Table 1. **Device summary**

Order code	Marking	Package	Packaging
2ST2121	2ST2121	TO-3	tray
	工币场网		



1 Absolute maximun rating

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-250	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	-250	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	-6	V
Ι _C	Collector current	-17	Α
I _{CM}	Collector peak current (t _P < 5ms)	-34	Α
P _{TOT}	Total dissipation at $T_c = 25 \text{ °C}$	250	W
T _{stg}	Storage temperature	-65 to 200	°C
TJ	Max. operating junction temperature	200	°C

Table 2. Absolute maximum rating

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	0.7	°C/W

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2 Electrical characteristics

(T_{case} = 25 °C; unless otherwise specified)

Symbol	Parameter	Test co	nditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current $(I_E = 0)$	V _{CB} = -250 V				-5	μA
I _{EBO}	Emitter cut-off current $(I_{\rm C}=0)$	V _{EB} = -6 V				-5	μA
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = -50 mA		-250			V
V _(BR) CBO	Collector-base breakdown voltage (I _E = 0)	l _C = -100 μA		-250			V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage $(I_{\rm C}=0)$	I _E = -1 mA		-6			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = -8 A	I _B = -800 mA			-3	V
V _{BE} ⁽¹⁾	Base-emitter on voltage	I _C = -7 A	$V_{CE} = -5 V$			-1.5	V
h _{FE}	DC current gain	I _C = -1 A I _C = -7 A	V _{CE} = -5 V V _{CE} = -5 V	80 35		160	
f _T	Transition frequency	I _C = -1 A	$V_{CE} = -5 V$		25		MHz

Table 4. Electrical characteristics

1. Pulsed duration = 300 $\mu s, \, duty \, cycle \leq 1.5\%$

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Figure 2.

2.1 Electrical characteristics (curves)

Safe operating area

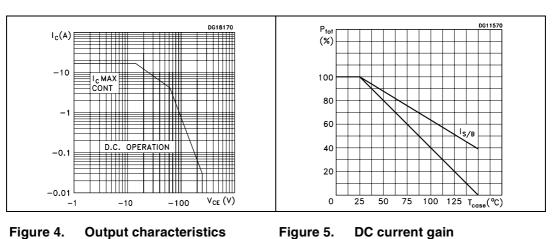


Figure 3.

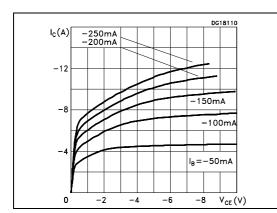


Figure 5. DC current gain

Derating curve

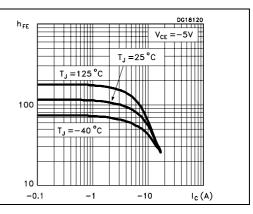
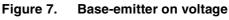
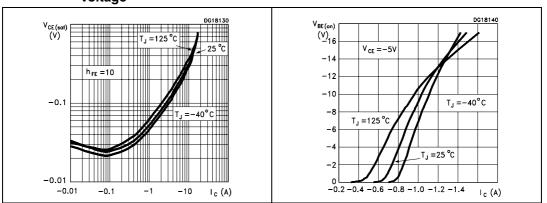


Figure 6. Collector-emitter saturation voltage





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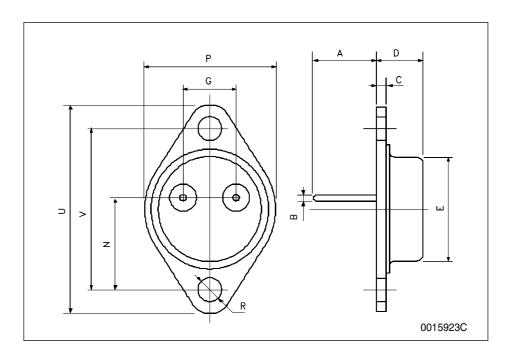
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3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



	TO-3 mechanical data			
DIM.		mm.		
DIW.	min.	typ	max.	
А	11.00		13.10	
В	0.97		1.15	
С	1.50		1.65	
D	8.32		8.92	
E	19.00		20.00	
G	10.70		11.10	
N	16.50		17.20	
Р	25.00		26.00	
R	4.00		4.09	
U	38.50		39.30	
V	30.00		30.30	





4 Revision history

Table 5.	Document revision	history

Date	Revision	Changes
11-Oct-2007	1	Initial release.
09-Dec-2007	2	Datasheet status changed from target specification to preliminary data.
16-May-2008	3	Added new graphics.
11-Jul-2008	4	Updated maximum operating junction temperature value.



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